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**PCT**NOTIFICATION CONCERNING  
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OF PRIORITY DOCUMENT

To:

SEMICONDUCTOR ENERGY LABORATORY CO.,  
LTD.  
398, Hase, Atsugi-shi  
Kanagawa 2430036  
JAPON

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Applicant <b>SEMICONDUCTOR ENERGY LABORATORY CO., LTD. et al</b>	

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The International Bureau of WIPO  
34, chemin des Colombettes  
1211 Geneva 20, Switzerland

Authorized officer

**Honda Masashi**

Facsimile No. +41 22 338 82 70

Facsimile No. +41 22 338 70 10  
Telephone No. +41 22 338 82 54

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(71) Applicant (for all designated States except US): SEMI-CONDUCTOR ENERGY LABORATORY CO., LTD.  
[JP/JP]; 398, Hase, Atsugi-shi, Kanagawa 2430036 (JP).

(72) Inventors; and

(75) Inventors/Applicants (for US only): TANAKA, Koichiro  
[JP/JP]; c/o SEMICONDUCTOR ENERGY LABORA-  
TORY CO., LTD., 398, Hase, Atsugi-shi, Kanagawa  
2430036 (JP). YAMAMOTO, Yoshitaki [JP/JP]; c/o  
SEMICONDUCTOR ENERGY LABORATORY CO.,  
LTD., 398, Hase, Atsugi-shi, Kanagawa 2430036 (JP).

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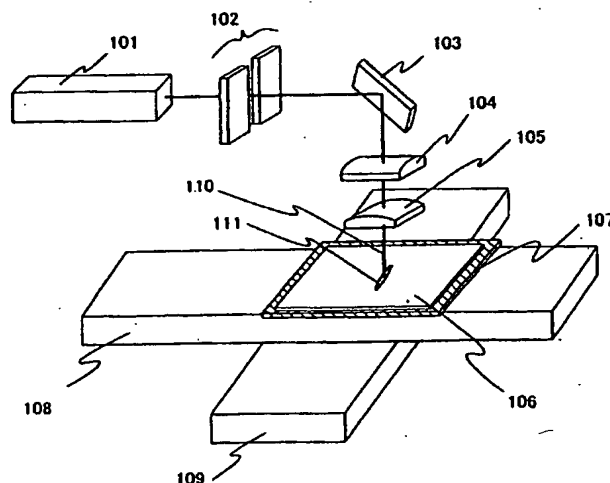
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ning of each regular issue of the PCT Gazette.

(54) Title: LASER IRRADIATION METHOD, LASER IRRADIATION APPARATUS AND METHOD FOR MANUFACTURING SEMICONDUCTOR DEVICE



(57) Abstract: In conducting laser annealing using a CW laser or a quasi-CW laser, productivity is not high as compared with an excimer laser and thus, it is necessary to further enhance productivity. According to the present invention, a fundamental wave is used without putting laser light into a non linear optical element, and laser annealing is conducted by irradiating a semiconductor thin film with pulsed laser light having a high repetition rate. A laser oscillator having a high output power can be used for laser annealing, since a non linear optical element is not used and thus light is not converted to a harmonic. Therefore, the width of a region having large grain crystals that is formed by scanning once can be increased, and thus the productivity can be enhanced dramatically.

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